

## 6.730 Physics for Solid State Applications

### Recitation 1: Free Electron Gas and Density of States

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### Quantum Free Electron Gas Crystal as Infinite Well Potential

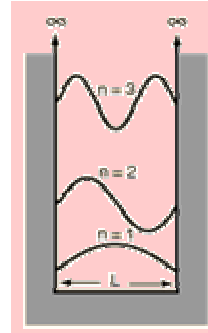
Electron confined in crystal of size  $L$  on a side  
no interaction with nuclei  
single particle approximation  
periodic boundary conditions

$$-\frac{\hbar^2 \nabla^2}{2m} \psi(\mathbf{r}) = E \psi(\mathbf{r})$$

$$\psi_{\mathbf{k}}(\mathbf{r}) = \frac{1}{\sqrt{V}} e^{i\mathbf{k} \cdot \mathbf{r}}$$

$$E(\mathbf{k}) = \frac{\hbar^2}{2m} |\mathbf{k}|^2 = \frac{\hbar^2}{2m} [k_x^2 + k_y^2 + k_z^2]$$

not for periodic b.c.



(hyperphysics.phy-astr.gsu.edu)

## Quantum Free Electron Gas Periodic Boundary Conditions

$$\psi(x + L, y, z) = \psi(x, y, z)$$

$$\psi(x, y + L, z) = \psi(x, y, z)$$

$$\psi(x, y, z + L) = \psi(x, y, z)$$

$$\begin{aligned} \psi(x+L, y, z) &= \frac{1}{\sqrt{V}} e^{ik_x(x+L)} e^{ik_y y} e^{ik_z z} = e^{ik_x L} \frac{1}{\sqrt{V}} e^{ik_x x} e^{ik_y y} e^{ik_z z} \\ &= e^{ik_x L} \psi(x, y, z) \end{aligned}$$

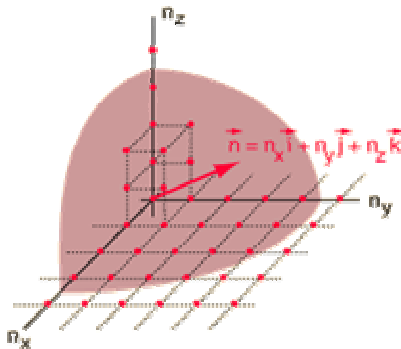
so that  $k_x = \frac{2\pi}{L} n_x$ ,  $k_y = \frac{2\pi}{L} n_y$ , and  $k_z = \frac{2\pi}{L} n_z$

and  $n_x, n_y, n_z$  are integers  $0, \pm 1, \pm 2, \pm 3 \dots$

$$E(\mathbf{k}) = E_{n_x, n_y, n_z} = \frac{\hbar^2}{2m} \left( \frac{2\pi}{L} \right)^2 [n_x^2 + n_y^2 + n_z^2]$$

## Limit for Large Crystals

$$E(\mathbf{k}) = E_{n_x, n_y, n_z} = \frac{\hbar^2}{2m} \left( \frac{2\pi}{L} \right)^2 [n_x^2 + n_y^2 + n_z^2]$$

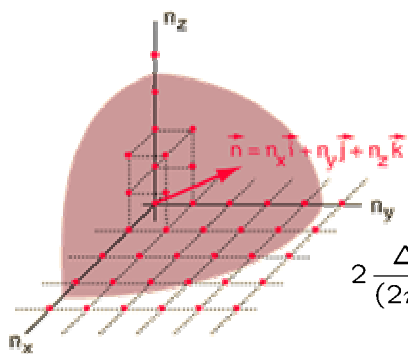


States fill up the lowest energies first, with two electrons (spin up and spin down) per energy level. The highest energy at zero temperature is denoted as  $E_{F0}$  and the highest  $\mathbf{k}$  vector as  $\mathbf{k}_F$ .

$$N = \sum_{k < k_F} 2 \quad \text{and} \quad E_{\text{total}} = \sum_{k < k_F} 2 \frac{\hbar^2 k^2}{2m}$$

## Limit for Large Crystals

$$N = \sum_{k < k_F} 2 \quad \text{and} \quad E_{\text{total}} = \sum_{k < k_F} 2 \frac{\hbar^2 k^2}{2m}$$



For large crystals we can use a macro-microvolume to do an integration rather than a sum.

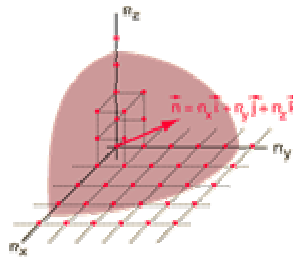
$$2 \frac{\Delta k_x}{(2\pi/L)} \frac{\Delta k_y}{(2\pi/L)} \frac{\Delta k_z}{(2\pi/L)} \rightarrow 2V \frac{d^3 k}{(2\pi)^3}$$

$$N \approx \underbrace{\iiint_{k < k_F}} 2V \frac{d^3 k}{(2\pi)^3}$$

$$E_{\text{total}} \approx \underbrace{\iiint_{k < k_F}} \frac{\hbar^2 k^2}{2m} 2V \frac{d^3 k}{(2\pi)^3}$$

## Zero-Temperature Limit Fermi Energy and Temperature

$$n = \frac{N}{V} = \frac{2}{(2\pi)^3} \frac{4\pi}{3} k_F^3$$



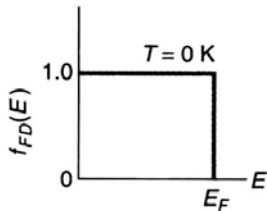
$$k_F = (3\pi^2 n)^{1/3} \sim 1 \text{ \AA}^{-1}$$

$$E_{F0} = \frac{\hbar^2}{2m} (3\pi^2 n)^{2/3} \sim 4 \text{ eV}$$

$$v_F = \frac{\hbar k_F}{m} \sim 10^8 \text{ cm/sec}$$

$$T_F = \frac{E_F}{k_B} \sim 50,000 \text{ K}$$

## Zero-Temperature Limit Electronic Energy



$$E_{\text{total}} \approx \underbrace{\int \int \int}_{k < k_F} \frac{\hbar^2 k^2}{2m} 2V \frac{d^3 \mathbf{k}}{(2\pi)^3}$$

$$\frac{E_{\text{total}}}{V} = \frac{3}{5} n E_{F0}$$

Average energy per electron:

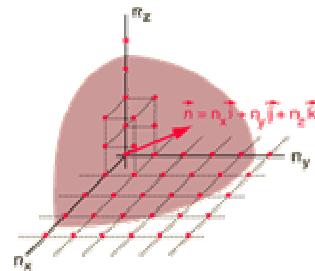
$$\frac{E_{\text{total}}}{N} = \frac{3}{5} E_{F0}$$

## Ensemble Averages at Zero Temperatures

Where  $F_k$  is any property of the electron

$$\frac{F_{\text{tot}}}{V} = \int_0^{E_{F0}} F_{\mathbf{k}} 2 \frac{d^3 \mathbf{k}}{(2\pi)^3}$$

$$\frac{F_{\text{tot}}}{V} = \int_0^{E_{F0}} F(E) g(E) dE$$



where  $g(E)$  is number of states at  $E$  per unit volume

By comparing the above two expressions...

$$\frac{2}{(2\pi)^3} 4\pi k^2 dk = g(E) dE \quad \implies \quad g(E) = \frac{mk}{\hbar^2 \pi^2} \quad \text{for} \quad E > 0$$

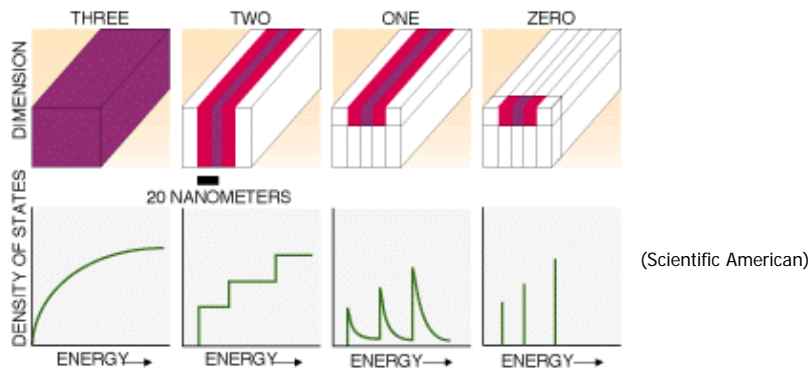
## Density of States in Large 3D Solid

$$g(E) = \frac{mk}{\hbar^2 \pi^2} \quad \text{for } E > 0$$

$$E(\mathbf{k}) = \frac{\hbar^2}{2m} |\mathbf{k}|^2 = \frac{\hbar^2}{2m} [k_x^2 + k_y^2 + k_z^2]$$

$$g(E) = \begin{cases} \frac{1}{2\pi^2} \frac{(2m)^{3/2}}{\hbar^2} E^{1/2} = \frac{3}{2} \frac{n}{E_{F0}} \left( \frac{E}{E_{F0}} \right)^{1/2} & E > 0 \quad \left[ \frac{\text{states}}{\text{J-m}^3} \right] \\ 0 & E < 0 \end{cases}$$

## Density of States in Different Solids



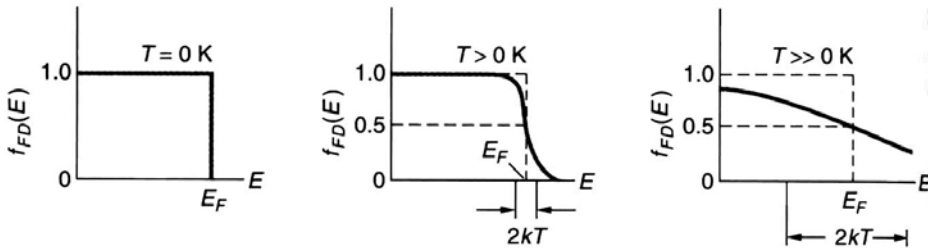
So at zero temperature

$$n = \int_0^{E_{F0}} g(E) dE \quad \text{and} \quad \frac{E}{V} = \int_0^{E_{F0}} E g(E) dE$$

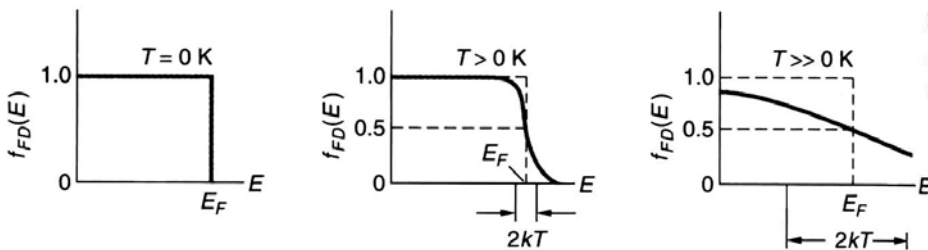
## Finite Temperature Limit

Probability of a particular energy level being occupied by an electron:

$$f(E - \mu) = \frac{1}{1 + e^{(E - \mu)/k_B T}}$$



## Finite Temperatures



$$n = \frac{N}{V} = \int_{-\infty}^{\infty} \frac{1}{1 + e^{(E_k - \mu)/k_B T}} 2 \frac{d^3 \mathbf{k}}{(2\pi)^3}$$

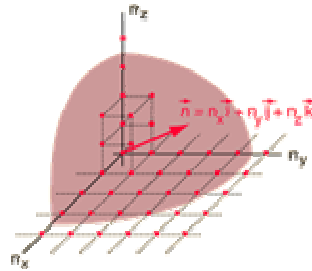
$$\frac{E_{\text{total}}}{V} = \int_{-\infty}^{\infty} E_k \frac{1}{1 + e^{(E_k - \mu)/k_B T}} 2 \frac{d^3 \mathbf{k}}{(2\pi)^3}$$

## Ensemble Averages at Finite Temperatures

Where  $F_k$  is any property of the electron

$$\frac{F_{\text{tot}}}{V} = \int_{-\infty}^{\infty} F_k \frac{1}{1 + e^{(E_k - \mu)/k_B T}} \frac{d^3k}{(2\pi)^3}$$

$$\frac{F_{\text{tot}}}{V} = \int_{-\infty}^{\infty} F(E)g(E) \frac{1}{1 + e^{(E - \mu)/k_B T}} dE$$



where  $g(E)$  is number of states at  $E$  per unit volume.  
It is the same as at zero temperature.

By comparing the above two expressions...

$$\frac{2}{(2\pi)^3} 4\pi k^2 dk = g(E) dE \quad \Rightarrow \quad g(E) = \frac{mk}{\hbar^2 \pi^2} \quad \text{for} \quad E > 0$$